

Application No.: 10/810,070

2

Docket No.: 577182000100

AMENDMENTS TO THE CLAIMS

Claim 1 (original): A method of customizing a polishing pad for chemical mechanical planarization of a substrate, the method comprising:

- obtaining one or more characteristics of a structure on a substrate; and
- selecting a value for one or more chemical or physical properties for a pad to be used in chemical mechanical planarization of the substrate based on the obtained one or more characteristics of the structures on the substrate.

Claim 2 (original): The method of claim 1, wherein the one or more characteristics of a structure includes a size of the structure.

Claim 3 (original): The method of claim 1, wherein the one or more characteristics of a structure includes a pattern density of the structure.

Claim 4 (original): The method of claim 1, wherein the one or more characteristics of a structure includes film material and a number of different materials.

Claim 5 (original): The method of claim 1, wherein one or more chemical or physical properties for the pad includes hardness, thickness, surface grooving, porosity, thickness, Youngs modulus, compressibility, or asperity of the pad.

Claim 6 (original): The method of claim 1, wherein selecting a value for one or more chemical or physical properties for a pad comprises:

pa-1026556 v4

Application No.: 10/810,070

3

Docket No.: 577182000100

performing a simulation of planarization of the substrate with a model of a CMP process using the pad with a range of values for the one or more chemical or physical properties of the pad; and

selecting a value for the one or more chemical or physical properties based on the simulation.

Claim 7 (original): The method of claim 6, further comprising:
providing a pattern density and a deposition bias as inputs to the model of a CMP process.

Claim 8 (original): The method of claim 6, further comprising:
obtaining a planarization length from the model of a CMP process; and
performing a sensitivity analysis to determine a correlation between planarization length and the one or more chemical or physical properties of the pad.

Claim 9 (original): The method of claim 8, wherein the value for the one or more chemical or physical properties is selected based on the determined correlation between planarization length and the one or more chemical or physical properties of the pad to optimize planarization length.

Claim 10 (original): The method of claim 6, further comprising:
identifying dishing and/or erosion from the model of a CMP process; and
performing a sensitivity analysis to determine a correlation between the one or more chemical or physical properties of the pad and dishing and/or erosion.

pa-1026556 v4

Application No.: 10/810,070

4

Docket No.: 577182000100

Claim 11 (original): The method of claim 10, wherein the value for the one or more chemical or physical properties is selected based on the determined correlation between the one or more chemical or physical properties of the pad and dishing and/or erosion to reduce dishing and/or erosion.

Claim 12 (original): The method of claim 6, further comprising:
identifying over-polishing and/or under-polishing from the model of a CMP process; and
performing a sensitivity analysis to determine a correlation between the one or more chemical or physical properties of the pad and over-polishing and/or under-polishing.

Claim 13 (original): The method of claim 12, wherein the value for the one or more chemical or physical properties is selected based on the determined correlation between the one or more chemical or physical properties of the pad and over-polishing and/or under-polishing to reduce over-polishing and/or under-polishing.

Claim 14 (original): The method of claim 1, wherein the structure is an optoelectronic device.

Claim 15 (original): The method of claim 1, wherein the substrate is a magnetic disk, an optical disk, a ceramic substrate, or a nano-composite substrate.

Claim 16 (original): A method of customizing a polishing pad for chemical mechanical planarization of a semiconductor wafer, the method comprising:
obtaining one or more characteristics of a chip;

pa-1026556 v4

Application No.: 10/810,070

5

Docket No.: 577182000100

performing a simulation of a chemical mechanical planarization of the wafer with a model of a CMP process using the obtained one or more characteristics of the chip and a range of values for the one or more chemical or physical properties of the pad; and

selecting a value for one or more chemical or physical properties for a pad based on the simulation.

Claim 17 (original): The method of claim 16, wherein the one or more characteristics of the chip includes a pattern density of the chip.

Claim 18 (original): The method of claim 17, wherein one or more chemical or physical properties for the pad includes hardness, thickness, surface grooving, porosity, thickness, Youngs modulus, compressibility, or asperity of the pad.

Claim 19 (original): The method of claim 16, further comprising:
obtaining a planarization length from the model of a CMP process; and
performing a sensitivity analysis to determine a correlation between planarization length and the one or more chemical or physical properties of the pad.

Claim 20 (original): The method of claim 19, wherein the value for the one or more chemical or physical properties is selected based on the determined correlation between planarization length and the one or more chemical or physical properties of the pad to optimize planarization length.

Claim 21 (original): The method of claim 16, further comprising:
identifying dishing and/or erosion from the model of a CMP process; and

pa-1026556 v4

Application No.: 10/810,070

6

Docket No.: 577182000100

performing a sensitivity analysis to determine a correlation between the one or more chemical or physical properties of the pad and dishing and/or erosion.

Claim 22 (original): The method of claim 21, wherein the value for the one or more chemical or physical properties is selected based on the determined correlation between the one or more chemical or physical properties of the pad and dishing and/or erosion to reduce dishing and/or erosion.

Claim 23 (original): The method of claim 16, further comprising:
identifying over-polishing and/or under-polishing from the model of a CMP process; and
performing a sensitivity analysis to determine a correlation between the one or more chemical or physical properties of the pad and over-polishing and/or under-polishing.

Claim 24 (original): The method of claim 23, wherein the value for the one or more chemical or physical properties is selected based on the determined correlation between the one or more chemical or physical properties of the pad and over-polishing and/or under-polishing to reduce over-polishing and/or under-polishing.

Claim 25 (currently amended): A method of customizing ~~of tribological or material~~ properties of a pad used in ~~[[a]]~~ chemical mechanical polishing (CMP) ~~process~~ to planarize a metal or dielectric film ~~having varying topographic or material characteristics on a substrate, the method~~ comprising:

selecting a value for one or more chemical or physical properties of the pad to compensating
compensate for pattern density effects ~~[[for]]~~ of the different chip or substrate architectures during
the CMP process; and

pa-1026556 v4

Application No.: 10/810,070

7

Docket No.: 577182000100

optimizing the pad for a derived planarization length, response characteristics for dishing and/or erosion, or final step height at specific pattern features to attain local and global planarization of the chip or substrate.

Claim 26 (currently amended): The method of claim 25, wherein the optimization is performed ~~during~~ for planarization of a silicon integrated circuit.

Claim 27 (currently amended): The method of claim 25, wherein the optimization is performed ~~during~~ for planarization of an optoelectronic device.

Claim 28 (currently amended): The method of claim 25, wherein the optimization is performed ~~during~~ for planarization of a magnetic or optical disk.

Claim 29 (currently amended): The method of claim 25, wherein the optimization is performed ~~during~~ for planarization of film on a ceramic or nano-composite substrate.

Claim 30 (original): A polishing pad for chemical mechanical planarization of a semiconductor wafer, the pad having:

one or more chemical or physical properties, wherein a value for the one or more chemical or physical properties is selected based on one or more characteristics of the chip.

Claim 31 (original): The pad of claim 30, wherein the value for the one or more chemical or physical properties is selected by:

obtaining a pattern density of the chip;

pa-1026556 v4

Application No.: 10/810,070

8

Docket No.: 577182000100

performing a simulation of a chemical mechanical planarization of the wafer with a model of a CMP process using the obtained pattern density of the chip and a range of values for the one or more chemical or physical properties of the pad; and

selecting a value for one or more chemical or physical properties based on the simulation.

pa-1026556 v4